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Sheet 1 of 1

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Atty.Docket No.: 0756-1139	Serial No. Not Yet Assigned <u>08/355,652</u>
Applicant: Shunpei YAMAZAKI et al.	
Filing Date: December 14, 1994	Group: 1104

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

CC	Sameshima et al., "XeCl excimer laser annealing used to fabricate poly-si TFTs, Mat. Res. Soc. Symp. Proc., vol. 71, 1986, pp. 435-440.
CC	Corey et al., "A shallow junction submicrometer PMOS process without high temperature anneals", IEEE electron device letters, vol. 9, no. 10, Oct. 1988, pp. 542-544.
CC	"Fabrication of Submicrometer MOSFET's Using Gas Immersion Laser Doping (GILD) IEEE ELECTRON DEVICE LETTERS Vol. EDL-7, No. 7, pp. 440-442

Examiner Chandra Chaudhari Date Considered

7-95

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.